

AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior versions, and listings, of claims in the application:

Claims 1-23 (Canceled)

24. (Previously presented) A nitride based heterostructure device comprising:

- a substrate;
- a buffer layer directly on the substrate, wherein the buffer layer includes In;
- a first layer including GaN directly on the buffer layer;
- a second layer directly on the first layer, wherein the second layer includes AlGa_N; and
- a quaternary layer directly on the second layer, wherein the quaternary layer includes AlInGa_N.

25. (Previously presented) The device of claim 24, wherein the substrate includes one of the group comprising sapphire, SiC, ZnO, a spinel substrate, Si, anodized alumina, and AlN.

26. (Previously presented) The device of claim 24, wherein the quaternary layer includes about a 20% to about 30% molar fraction of Al.

27. (Previously presented) The device of claim 26, wherein the quaternary layer further includes about a 2% to about 5% molar fraction of In.

28. (Previously presented) The device of claim 24, wherein the first layer further includes In.

29. (Previously presented) A nitride based heterostructure device comprising:

- a substrate;

- a buffer layer directly on the substrate, wherein the buffer layer includes In;

- a ternary layer directly on the buffer layer, wherein the ternary layer includes Ga, In, and N; and

- a quaternary layer directly on the ternary layer, wherein the quaternary layer includes Ga, Al, In, and N.

30. (Previously presented) The device of claim 29, wherein the buffer layer includes Al and N.

Claims 31-34 (Canceled)

35. (Previously presented) A nitride based heterostructure device comprising:

- a substrate;

- a buffer layer on the substrate, wherein the buffer layer includes In;

- a first layer including GaN on the buffer layer;

- a second layer on the first layer, wherein the second layer includes AlGa_{0.5}N_{0.5}; and

- a quaternary layer on the second layer, wherein the quaternary layer includes AlInGa_{0.5}N_{0.5}, wherein the quaternary layer includes about a 20% to about 30% molar fraction of Al.

36. (Previously presented) The device of claim 35, wherein the quaternary layer further includes about a 2% to about 5% molar fraction of In.